PCN Number: 20:			1905	90509001.2			PCN	PCN Date: May 13, 2019			
Title: Transfer of select			DLM devices from GFAB to FFAB Wafer Fab site								
Customer Contact:				PCN Manager Dept:			Quality Services				
Proposed 1 st Ship Date:			:	Nov	ov 13, 2019 Estimated Samp Availability:			Date provided at sample request.			
Change Type:											
Assembly Site					Assembly Process				Assembly Materials		
Design					Electrical Specification			Mechanical Specification			
Test Site					Packing/Shipping/Labeling				Test Pro	ocess	
Wafer Bump Site					Wafer Bump Material				Wafer E	Bump Process	
				\boxtimes	Wafer Fab Materials				Wafer F	ab Process	
					Part number change					·	
PCN Details											

Description of Change:

This change notification is to announce the transfer of select DLM devices from GFAB to the FFAB (FR-BIP-1) Wafer Fab site for the selected devices listed in the "Product Affected" section.

	Current Fab Site		New Fab Site			
Current Fab Site	Process	Wafer Diameter	New Fab Site	Process	Wafer Diameter	
GFAB6	DLM	150 mm	FFAB	DLM	200 mm	

Qual details are provided in the Qual Data Section.

Reason for Change:

Greenock, Scotland (GFAB) Wafer Fab site closure

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Changes to product identification resulting from this PCN:

Current

Chip Site	Chip Site Origin (20L)	Chip Site Country Code (21L)	Chip Site City
GFAB6	GF6	GBR	Greenock

New Fab Site

Chip Site	Chip Site Origin (20L)	Chip Site Country Code (21L)	Chip Site City
FR-BIP-1	TID	DEU	Freising

Sample product shipping label (not actual product label)





(1P) SN74LS07NSR (D) 0336 31T)LOT: 3959047MLA 4W) TKY(1T) 7523483SI2 (20L) CSO: SHE (21L) CCO:USA (22L) ASO: MLA (23L) ACO: MYS (23L) ACO. MYS

Product Affected Group:

LM9061QDRQ1

Automotive Change Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Approved 7-May-2019 Product Attributes

Attributes	Qual Device: LM9061QDRQ1	QBS Device: LM2576HVT-5.0/NOPB
Automotive Grade Level	Grade 1	Grade 1
Operating Temp Range	-40 to +125 C	-40 to +125 C
Product Function	MOSFET Driver	Power Management
Wafer Fab Supplier	FFAB	FFAB
Die Revision	В	F
Assembly Site	MLA	TIEM
Package Type	SOIC	TO-220
Package Designator	D	KC
Ball/Lead Count	8	5

⁻ QBS: Qual By Similarity

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: LM9061QDRQ1	QBS Device: LM2576HVT-5.0/NOPB
Test Group A – Accelerated Environment Stress Tests								
PC	A1	JEDEC J-STD- 020 JESD22- A113	3	77	Preconditioning	Level 3-260C	All pass	-
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0	-
AC	A3	JEDEC JESD22- A102	3	77	Autoclave 121C	96 Hours	3/231/0	-
тс	Α4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle, - 65/150C	500 Cycles	3/231/0	-
			3	5	Post-TC Bond Pull	TC 500 Cycles	3/15/0	-

⁻ Qual Device LM9061QDRQ1 is qualified at LEVEL3-260C

Тур	e #	:	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: LM9061QDRQ1	QBS Device: LM2576HVT-5.0/NOPB
PTO	C A	5	JEDEC JESD22- A105	1	45	Power Temperature Cycle, -40/125C	1000 Cycles	N/A	-
HTS	SL A	6	JEDEC JESD22- A103	1	45	High Temp Storage Bake 150C	1000 Hours	3/231/0	-
			Test Group B						
нтс	DL B	1	JEDEC JESD22- A108	3	77	Life Test, 125C	1000 Hours	1/77/0	3/231/0
EFF	R B	2	JEDEC JESD22- A108	3	800	Early Life Failure Rate, 125C	48 Hours	2/1600/0	3/2400/0
EDI	R B	3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A	-
			Test Group	C – Pack	age Asse	mbly Integrity Tests			
WB	S C	1	AEC Q100-001	1	30	Wire Bond Shear (Cpk>1.67)	Wires	1/30/0	-
WB	SP C	2	MIL-STD883 Method 2011	1	30	Wire Bond Pull (Cpk>1.67)	Wires	1/30/0	-
SE) C:	3	JEDEC JESD22- B102	1	15	Solderability	Pb free, 8 Hours Steam Age	3/45/0	-
PD) C4	4	JEDEC JESD22- B100 and B108	3	10	Physical Dimensions (Cpk>1.67)	-	3/30/0	-
SB	S C	5	AEC Q100-010	3	50	Solder Ball Shear (Cpk>1.67)	Solder Balls	N/A	-
			Test Group	D – Die	Fabrication	on Reliability Tests			
EN	I Di	1	JESD61	-	-	Electromigration	-	-	-
TDD	DB D2	2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	1	-
нс	Di Di	3	JESD60 & 28	-	-	Hot Injection Carrier	-	-	-
NBT	TI D4	4	-	-	-	Negative Bias Temperature Instability	-	-	-
SN	1 D	5	-	-	-	Stress Migration	-	-	-
	Test Group E – Electrical Verification Tests								
HBI	M E	2	AEC Q100-002	1	3	ESD - HBM - Q100	2500 V	3/9/0	-
CDI	M E	3	AEC Q100-011	1	3	ESD - CDM - Q100	1500 V	3/9/0	-
LU	J E4	4	AEC Q100-004	1	6	Latch-up	125C	3/18/0	-
EC) E	5	AEC Q100-009	3	30	Auto Electrical Distributions	Cpk>1.67 Room, hot, and cold test	3/90/0	-

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED

Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST

Green/Pb-free Status:

Qualified Pb-Free (SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
WW PCN Team	PCN www admin_team@list.ti.com